

STD826

PNP MEDIUM POWER TRANSISTOR

Features

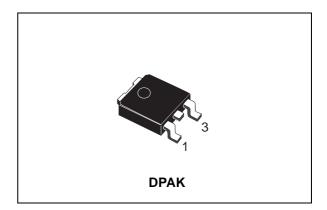
- SURFACE MOUNTING DEVICE IN MEDIUM POWER DPAK PACKAGE
- AVAILABLE IN TAPE & REEL PACKING
- IN COMPLIANCE WITH THE 2002/93/EC EUROPEAN DIRECTIVE

Applications

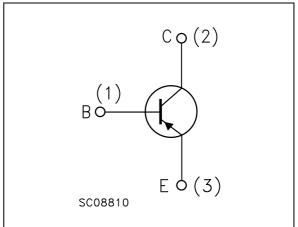
- VOLTAGE REGULATION
- RELAY DRIVER
- GENERIC SWITCH

Description

The STD826 is PNP transistor manufactured using planar Technology resulting in rugged high performance devices.



Internal Schematic Diagram



Order codes

Part Number	Marking	Package	Packing
STD826T4	STD826T4 D826		Tape & reel

1 Absolute Maximum Ratings

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage (I _E = 0)	-60	V
V _{CEO}	Collector-Emitter Voltage (I _B = 0)	-30	V
V _{EBO}	Collector-Base Voltage ($I_C = 0$)	-5	V
۱ _C	Collector Current	-3	Α
I _{CM}	Collector Peak Current (t _P < 5ms)	-6	А
Ι _Β	Base Current	-1	Α
I _{BM}	Base Peak Current (t _P < 5ms)	-2	А
P _{TOT}	Total dissipation at $T_c = 25^{\circ}C$	15	W
T _{STG}	Storage Temperature	-65 to 150	°C
ТJ	Max. Operating Junction Temperature	150	°C

Table 1. Absolute Maximum Rating

Table 2. Thermal Data

Symbol	Parameter	Value	Unit
R _{thJ-case}	Thermal Resistance Junction-Case Max	8.33	°C/W

2 Electrical Characteristics

Symbol	Deremeter	Test Canditia		Min	Turn	Max	l Init
Symbol	Parameter	Test Conditio	ns	Min.	Тур.	Max.	Unit
I _{CES}	Collector Cut-off Current	V _{CE} = -60V				-10	μA
	(V _{BE} = 0)						
I _{CEO}	Collector Cut-off Current	V _{CE} = -30V				-100	μA
	$(I_{B} = 0)$						
I _{EBO}	Emitter Cut-off Current	V _{EB} = -5V				-10	μA
220	$(I_{\rm C} = 0)$						
M	Collector-Base	I _C = -100μA		-60			V
V _{(BR)CBO}	Breakdown Voltage (I _E = 0)						
V _{(BR)CEO}	Collector-Emitter Breakdown	I _C = -10 mA		-30			V
Note: 1	Voltage (I _B = 0)						
M	Collector-Emitter Breakdown	I _E = -100 μA		-5			V
V _{(BR)EBO}	Voltage (I _C = 0)						
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -1 A I	_B = -50 mA			-0.4	V
Note: 1		$I_{\rm C} = -2 {\rm A} \qquad I_{\rm B}$	= -100 mA			-0.7	V
		I _C = -3 A I _B	= -150 mA			-1.1	V
V _{BE(sat)}		$I_{\rm C} = -2$ A $I_{\rm B}$	= -100 mA			-1.2	V
Note: 1	Base-Emitter Saturation Voltage						
h _{FE}	DC Current Gain	I _C = -100 mA V	′ _{CE} = -2 V	100		300	
		-	′ _{CE} = -2 V	80			
		•	′ _{CE} = -2 V	30			
f _T	Transistor Frequency	V _{CE} = -10 V I _c	_c = - 0.1 A		100		MHz

Table 3.Electrical Characteristics ($T_{CASE} = 25^{\circ}C$; unless otherwise specified)

Note: 1 Pulsed duration = $300 \ \mu$ s, duty cycle $\leq 1.5\%$.



2.1 Electrical characteristics (curve)

Figure 1. DC Current Gain

Figure 2. DC Current Gain

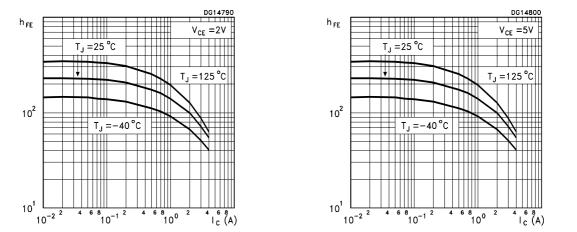


Figure 3. Collector-emitter saturation voltage Figure 4. Base-emitter saturation voltage

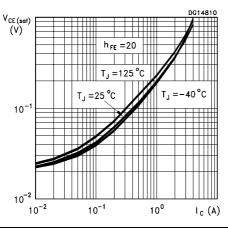
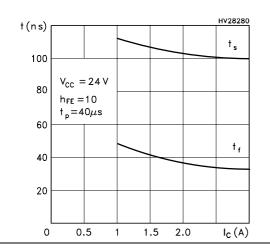


Figure 5. Switching times on resistive load



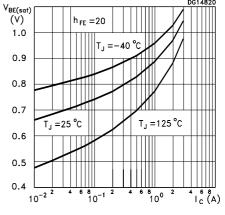


Figure 6. Switching times resistive on load

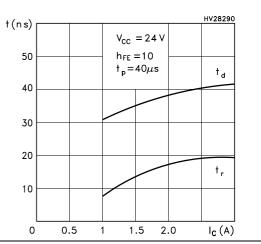
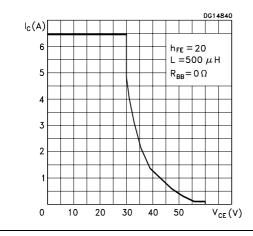




Figure 7. Reverse biased area





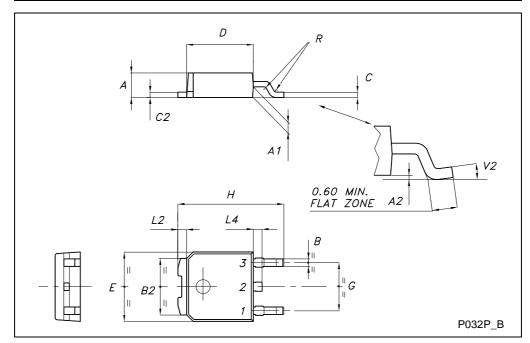
3 Package Mechanical Data

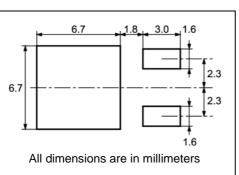
In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com



DIM.	mm				inch	
DIN.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	2.20		2.40	0.087		0.094
A1	0.90		1.10	0.035		0.043
A2	0.03		0.23	0.001		0.009
В	0.64		0.90	0.025		0.035
B2	5.20		5.40	0.204		0.213
С	0.45		0.60	0.018		0.024
C2	0.48		0.60	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.60	0.252		0.260
G	4.40		4.60	0.173		0.181
н	9.35		10.10	0.368		0.398
L2		0.8			0.031	
L4	0.60		1.00	0.024		0.039
V2	0°		8°	0°		0°

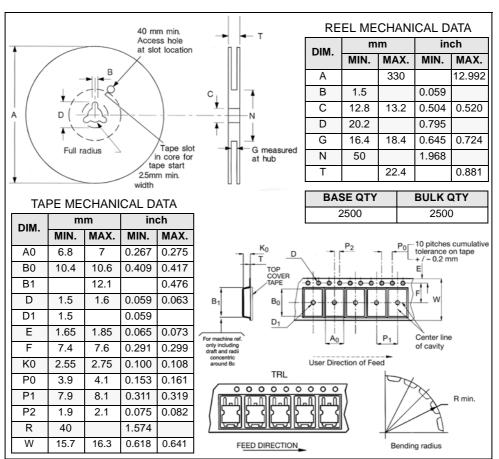
TO-252 (DPAK) MECHANICAL DATA







TAPE AND REEL SHIPMENT





STD826

4 Revision History

Date	Revision	Changes
03-Aug-2005	1	Initial release.



Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

> The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners

> > © 2005 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan -Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com

10/10

